200mW High Power Laser Diode

Description
The SLD302V is a gain-guided, high-power laser diodes fabricated by MOCVD.
MOCVD: Metal Organic Chemical Vapor Deposition

Features
- High power
  Recommended power output \( P_0 = 180 \text{mW} \)
- Low operating current

Applications
- Solid state laser excitation
- Medical use

Structure
GaAlAs double-hetero-type laser diode

Operating Lifetime
MTTF 10,000H (effective value) at \( P_0 = 180 \text{mW}, T_c = 25\degree \text{C} \)

Absolute Maximum Ratings \((T_c = 25\degree \text{C})\)
- Optical power output \( P_0 \) 200 mW
- Reverse voltage \( V_R \) LD 2 V
  PD 15 V
- Operating temperature \( T_{opr} \) –10 to +50 °C
- Storage temperature \( T_{stg} \) –40 to +85 °C

Warranty
This warranty period shall be 90 days after receipt of the product or 1,000 hours operation time whichever is shorter.
Sony Quality Assurance Department shall analyze any product that fails during said warranty period, and if the analysis results show that the product failed due to material or manufacturing defects on the part of Sony, the product shall be replaced free of charge.
Laser diodes naturally have differing lifetimes which follow a Weibull distribution.
Special warranties are also available.

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Electrical and Optical Characteristics (Tc: Case temperature, Tc = 25°C)

<table>
<thead>
<tr>
<th>Item</th>
<th>Symbol</th>
<th>Conditions</th>
<th>Min.</th>
<th>Typ.</th>
<th>Max.</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>Threshold current</td>
<td>Ith</td>
<td></td>
<td>150</td>
<td>200</td>
<td></td>
<td>mA</td>
</tr>
<tr>
<td>Operating current</td>
<td>Iop</td>
<td>Po = 180mW</td>
<td>350</td>
<td>500</td>
<td></td>
<td>mA</td>
</tr>
<tr>
<td>Operating voltage</td>
<td>Vop</td>
<td>Po = 180mW</td>
<td>1.9</td>
<td>3.0</td>
<td></td>
<td>V</td>
</tr>
<tr>
<td>Wavelength*1</td>
<td>λp</td>
<td>Po = 180mW</td>
<td>770</td>
<td>840</td>
<td></td>
<td>nm</td>
</tr>
<tr>
<td>Monitor current</td>
<td>Imon</td>
<td>Po = 180mW</td>
<td></td>
<td>0.3</td>
<td></td>
<td>mA</td>
</tr>
</tbody>
</table>

| Radiation angle (F. W. H. M.*) | Perpendicular | θ⊥ | Po = 180mW | 28 | 40 | degree |
|                               | Parallel      | θ∥ | Po = 180mW | 12 | 17 | degree |

Positional accuracy
- Position: ΔX, ΔY
- Angle: Δφ⊥

| Differential efficiency | ηD | Po = 180mW | 0.65 | 0.9 |      | mW/mA |

* F. W. H. M. : Full Width at Half Maximum

*1 Wavelength Selection Classification

<table>
<thead>
<tr>
<th>Type</th>
<th>Wavelength (nm)</th>
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<tbody>
<tr>
<td>SLD302V-1</td>
<td>785 ± 15</td>
</tr>
<tr>
<td>SLD302V-2</td>
<td>810 ± 10</td>
</tr>
<tr>
<td>SLD302V-3</td>
<td>830 ± 10</td>
</tr>
</tbody>
</table>

<table>
<thead>
<tr>
<th>Type</th>
<th>Wavelength (nm)</th>
</tr>
</thead>
<tbody>
<tr>
<td>SLD302V-21</td>
<td>798 ± 3</td>
</tr>
<tr>
<td>SLD302V-24</td>
<td>807 ± 3</td>
</tr>
<tr>
<td>SLD302V-25</td>
<td>810 ± 3</td>
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</tbody>
</table>

Handling Precautions
Eye protection against laser beams
The optical output of laser diodes ranges from several mW to 1W. However the optical power density of the laser beam at the diode chip reaches 1mW/cm². Unlike gas lasers, since laser diode beams are divergent, uncollimated laser diode beams are fairly safe at a laser diode. For observing laser beams, ALWAYS use safety goggles that block infrared rays. Usage of IR scopes, IR cameras and fluorescent plates is also recommended for monitoring laser beams safely.
Example of Representative Characteristics

- Optical power output vs. Forward current characteristics
- Optical power output vs. Monitor current characteristics
- Threshold current vs. Temperature characteristics
- Power dependence of far field pattern (parallel to junction)
- Power dependence of near field pattern
- Oscillation wavelength vs. Temperature characteristics
Differential efficiency vs. Temperature characteristics

Power dependence of polarization ratio

\[ \eta = \text{Differential efficiency [mW/mA]} \]

\[ T_c \text{ – Case temperature [°C]} \]

\[ P_0 \text{ – Optical power output [mW]} \]

\[ \text{Tc} = 25^\circ \text{C} \]
Power dependence of wavelength

\begin{align*}
\text{Tc} &= 25^\circ\text{C} \\
\text{Po} &= 40\text{mW}
\end{align*}

\begin{align*}
\text{Tc} &= 25^\circ\text{C} \\
\text{Po} &= 80\text{mW}
\end{align*}

\begin{align*}
\text{Tc} &= 25^\circ\text{C} \\
\text{Po} &= 120\text{mW}
\end{align*}

\begin{align*}
\text{Tc} &= 25^\circ\text{C} \\
\text{Po} &= 160\text{mW}
\end{align*}

\begin{align*}
\text{Tc} &= 25^\circ\text{C} \\
\text{Po} &= 200\text{mW}
\end{align*}
Temperature dependence of wavelength (Po = 180mW)
Package Outline

Unit: mm

M-248 (LO-11)

<table>
<thead>
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<th>SONY CODE</th>
<th>M-248</th>
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<td>EIAJ CODE</td>
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<td>JEDEC CODE</td>
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| PACKAGE MASS | 1.2g |

+Optical Distance = 2.55 ± 0.05